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Form PTO-1449		U.S. Department of Commerce	Attorney Docket No.	Serial No.	
		Patent and Trademark Office	5347-208	09/891,552	
·			Applicants:		
LIST OF DOCUMENTS CITED BY APPLICANT			Gerald Lucovsky et al.		
P E CUse several sheets if necessary)			Filing Date:	GAU:	
O	7	:	June 25, 2001	28145	
			g Author, Title, Date, Pertinent Pa		
	Wilk et al., High-K Gate Dielectrics: Current Status and Materials Properties Considerations, Journal of				
al		Applied Physics, Vol. 89, No. 10, May 15, 2001, pp. 5243-5275			
		Lucovsky et al., Microscopic Model for Enhanced Dielectric Constants in Low Concentration SiO2-Rich			
RAU		Noncrystalline Zr and Hf Silicate Alloys, Applied Physics Letters, Vol. 77, No. 18, October 30, 2000, pp.			
		2912-2914			
	3	, , , , , , , , , , , , , , , , , , , ,			
	Applications, IEDM, 2000, pp. 223-226				
4 Robertson et al., Band Offsets of Wide-Band-Gap Oxides				Future Electronic Devices, J.	
		Vac. Sci. Technol. B, Vol. 18, No. 3, Ma			
	5 Gusev et al., High-Resolution Depth Profiling in Ultrathin Al ₂ O ₃ Films on Si, Applied Physics Letters, Vol. No. 2, January 10, 2000, pp. 176-178				
	6	1 1 7 6 2 7 1 1 1			
	<u> </u>	IEEE Symposium on VLSI Technology, Digest of Technical Papers, pp. 16-17			
1	7	The state of the s			
1		AL ₂ O ₃ Thin Films on Si(100), Applied Physics Letters, Vol. 75, No. 25, December 20, 1999, pp. 4001-4003			
	8	Lucovsky, U.S. Serial No. 09/434,607, filed November 5, 1999			
	9	8)			
ı (Baumvol, Atomic Transport During Growth of Ultrathin Dielectrics on Silicon, Surface Science Reports, V				
36, pp. 1-166 19.99 Hinds et al., Investigation of Postoxidation Thermal Treatments of Si/SiO ₂ Interface in Re			6		
Hinds et al., Investigation of Postoxidation Thermal Treatments of Si/SiO ₂ Interface in Relationship			erface in Relationship to the		
		Kinetics of Amorphous Si Suboxide Decomposition, J. Vac. Sci. Technol. B, Vol. 16, No. 4, July/August 1998,			
-	12	pp. 2171-2176	(D	I T C P	
	12	Yasuda et al., Low-Temperature Formati			
		Plasma-Assisted Oxidation/Deposition P	rocess, J. vac. Sci. Technol. B, Vol.	10, No. 4, July/August 1992, pp.	
-	12	1844-1851	ania Pubblana at Paduard D	Voc Sci Technol A Vol C	
	13	Hersee et al., The Operation of Metalorg	anic buddiers at Keaucea Pressure, J	. vac. Sci. Technol. A, Vol. 8,	
-	14	No. 2, March/April 1990, pp. 800-804 Hunt et al., <i>The Absolute Determination of the Absolute D</i>	of Degenant Engaging for the De Jintin	Continue of Ductors L. P.	
n.	. / 14	Carbon, Fluorine, Magnesium, and Alum			
W 6	\mathcal{U}	No. 6, March 15, 1953, pp. 1283-1287	unum in ine Energy Kange Below 500	kev, rhysical Keview, vol. 89,	
	-	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1			

Examiner:

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